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Application No. <u>0943199</u>	Prepared by <u>M. RUSTIA</u>	Tracking Number <u>05995539</u>	
Examiner-GAU <u>NELM8-2818</u>	Date <u>09-28-04</u>	Week Date <u>08-16-04</u>	
	No. of queries <u>1</u>	<u>VPW</u>	

## JACKET

a. Serial No.	f. Foreign Priority	k. Print Claim(s)	p. PTO-1449
b. Applicant(s)	g. Disclaimer	l. Print Fig.	q. PTOL-85b
c. Continuing Data	h. Microfiche Appendix	m. Searched Column	r. Abstract
d. PCT	i. Title	n. PTO-270/328	s. Sheets/Figs
e. Domestic Priority	j. Claims Allowed	o. PTO-892	t. Other

## SPECIFICATION

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- f. Duplicate Text
- g. Brief Description
- h. Sequence Listing
- i. Appendix
- j. Amendments
- k. Other

## CLAIMS

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SUBSTITUTE for form 1449A/PTO  <b>INFORMATION DISCLOSURE          STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>			<b>Complete If Known</b>		
			Application Number	09/943,199	
			Filing Date	August 29, 2001	
			First Named Inventor	Kristy A. Campbell	
			Art Unit	2818	
			Examiner Name	D. Vu	
Sheet	1	of	5	Attorney Docket Number	M4065.0704/P704

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	AA	2002/0000666	1/3/2002	Kozicki et al.	
	AB	2002/0072188	6/13/2002	Gilton	
	AC	2002/0106849	08/08/2002	Moore	
	AD	2002/0123169	09/05/2002	Moore et al.	
	AE	2002/0123170	09/05/2002	Moore et al.	
	AF	2002/0123248	09/05/2002	Moore et al.	
	AG	2002/0127888	09/12/2002	Moore et al.	
	AH	2002/0132417	09/09/2002	Li	
	AI	2002/0160551	10/31/2002	Harshfield	
	AJ	2002/0163828	11/07/2002	Krieger et al.	
	AK	2002/0168820	11/2002	Kozicki	
	AL	2002/0168852	11/2002	Kozicki	
	AM	2002/0190289	12/19/2002	Harshfield et al.	
	AN	2002/0190350	12/19/2002	Kozicki et al.	
	AO	2003/0001229	01/02/2003	Moore et al.	
	AP	2003/0027416	02/06/2003	Moore	
	AQ	2003/0032254	02/13/2003	Gilton	
	AR	2003/0035314	02/20/2003	Kozicki	
	AS	2003/0035315	02/20/2003	Kozicki	
	AT	2003/0038301	02/27/2003	Moore	
	AU	2003/0043631	03/06/2003	Gilton et al.	
	AV	2003/0045049	3/2003	Campbell et al.	
	AW	2003/0045054	3/2003	Campbell et al.	
	AX	2003/0047765	03/13/2003	Campbell	
	AY	2003/0047772	03/13/2003	Li	
	AZ	2003/0047773	03/13/2003	Li	
	AA1	2003/0048519	03/13/2003	Kozicki	
	AB1	2003/0048744	3/2003	Ovshinsky et al.	
	AC1	2003/0049912	03/13/2003	Campbell et al.	
	AD1	2003/0068861	4/2003	Li et al.	
	AE1	2003/0068862	4/2003	Li et al.	
	AF1	2003/0095426	05/22/2003	Hush et al.	
	AG1	2003/0098497	5/2003	Moore et al.	
	AH1	2003/0107105	6/2003	Kozicki	
	AI1	2003/0117831	06/26/2003	Hush	
	AJ1	2003/0128612	07/10/2003	Moore et al.	
	AK1	2003/0137869	07/24/2003	Kozicki	
	AL1	2003/0143782	07/31/2003	Gilton et al.	
	AM1	2003/0155589	08/21/2003	Campbell et al.	
	AN1	2003/0155608	08/21/2003	Campbell et al.	
	AO1	2003/0156447	08/21/2003	Kozicki	
	AP1	2003/0156463	08/21/2003	Casper et al.	
	AQ1	2003/0209728	11/13/2003	Kozicki et al.	



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			Art Unit	2818	
			Examiner Name	D. Vu	
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AR1	2003/0209971	11/13/2003	Kozicki et al	
AS1	2003/0210564	11/13/2003	Kozicki et al	
AT1	2003/0212724	11/2003	Ovshinsky et al.	
AU1	2003/0212725	11/2003	Ovshinsky et al.	
AV1	2004/0035401	2/2004	Ramachandran et al.	
AW1	RE 37,259E	7/2001	Ovshinsky	
AX1	3,271,591	9/1986	Ovshinsky	
AY1	3,961,314	6/1976	Klose et al.	
AZ1	3,966,317	6/1976	Wacks et al.	
AA2	3,983,542	11/1976	Ovshinsky	
AB2	3,988,720	10/1976	Ovshinsky	
AC2	4,177,474	12/1979	Ovshinsky	
AD2	4,267,261	5/1981	Hailman et al.	
AE2	4,316,946	1/1982	Masters, et al.	
AF2	4,597,162	7/1986	Johnson et al.	
AG2	4,608,296	8/1986	Keem et al.	
AH2	4,637,895	1/1987	Ovshinsky et al.	
AI2	4,646,266	2/1987	Ovshinsky et al.	
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AL2	4,670,763	8/1987	Ovshinsky et al.	
AM2	4,671,618	06/09/1987	Wu et al.	
AN2	4,673,957	6/1987	Ovshinsky et al.	
AO2	4,678,679	7/1987	Ovshinsky	
AP2	4,696,758	9/1987	Ovshinsky et al.	
AQ2	4,698,234	10/1987	Ovshinsky et al.	
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AS2	4,728,406	3/1988	Banerjee et al.	
AT2	4,737,379	4/1988	Hudgens et al.	
AU2	4,766,471	8/1988	Ovshinsky et al.	
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AW2	4,775,425	10/1988	Guha et al.	
AX2	4,788,594	11/1988	Ovshinsky et al.	
AY2	4,800,526	01/24/1989	Lewis	
AZ2	4,809,044	2/1989	Pryor et al.	
AA3	4,818,717	4/1989	Johnson et al.	
AB3	4,843,443	6/1989	Ovshinsky et al.	
AC3	4,845,533	7/1989	Pryor et al.	
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AJ3	5,296,716	3/1994	Ovshinsky et al.	
AK3	5,314,772	5/24/1994	Kozicki	
AL3	5,335,219	8/1994	Ovshinsky et al.	
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First Named Inventor	Kristy A. Campbell
Art Unit	2818
Examiner Name	D. Vu
Attorney Docket Number	M4065.0704/P704

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A03	5,406,509	4/1995	Ovshinsky et al.
AP3	5,414,271	5/1995	Ovshinsky et al.
AQ3	5,534,711	7/1996	Ovshinsky et al.
AR3	5,534,712	7/1996	Ovshinsky et al.
AS3	5,536,947	7/1996	Klersy et al.
AT3	5,543,737	8/1996	Ovshinsky
AU3	5,591,501	1/1997	Ovshinsky et al.
AV3	5,596,522	1/1997	Ovshinsky et al.
AW3	5,687,112	11/1997	Ovshinsky
AX3	5,694,054	12/1997	Ovshinsky et al.
AY3	5,714,768	2/1998	Ovshinsky et al.
AZ3	5,814,527	9/29/1998	Wolstenholme et al
AA4	5,818,749	10/06/1998	Harshfield
AB4	5,825,046	10/1998	Czubatyj et al.
AC4	5,851,882	12/22/1998	Harshfield
AD4	5,869,843	2/9/1999	Harshfield
AE4	5,912,839	6/1999	Ovshinsky et al.
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AG4	6,011,757	1/2000	Ovshinsky
AH4	6,031,287	2/29/2000	Harshfield
AI4	6,072,716	06/06/2000	Jacobson et al.
AJ4	6,087,674	7/2000	Ovshinsky et al.
AK4	6,141,241	10/2000	Ovshinsky et al.
AL4	6,339,544	1/2002	Chiang et al.
AM4	6,404,665	6/2002	Lowery et al.
AN4	6,429,064	8/2002	Wicker
AO4	6,437,383	8/2002	Xu
AP4	6,440,837	8/27/2002	Harshfield
AQ4	6,462,984	10/2002	Xu et al.
AR4	6,473,332	10/2002	Ignatiev et al.
AS4	6,480,438	11/2002	Park
AT4	6,487,106	11/26/2002	Kozicki
AU4	6,487,113	11/2002	Park et al.
AV4	6,501,111	12/2002	Lowery
AW4	6,507,061	1/2003	Hudgens et al.
AX4	6,511,862	1/2003	Hudgens et al.
AY4	6,511,867	1/2003	Lowery et al.
AZ4	6,512,241	1/2003	Lai
AA5	6,514,805	2/2003	Xu et al.
AB5	6,531,373	3/2003	Gill et al.
AC5	6,534,781	3/2003	Dennison
AD5	6,545,287	4/2003	Chiang
AE5	6,545,907	4/2003	Lowery et al.
AF5	6,555,860	4/2003	Lowery et al.
AG5	6,563,164	5/2003	Lowery et al.
AH5	6,566,700	5/2003	Xu
AI5	6,567,293	5/2003	Lowery et al.
AJ5	6,569,705	5/2003	Chiang et al.
AK5	6,570,784	5/2003	Lowery



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Examiner Name	D. Vu
Attorney Docket Number	M4065.0704/P704

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AL5	6,576,921	6/2003	Lowery
AM5	6,586,761	7/2003	Lowery
AN5	6,589,714	7/2003	Maimon et al.
AO5	6,590,807	7/2003	Lowery
AP5	6,593,176	7/2003	Dennison
AQ5	6,597,009	7/2003	Wicker
AR5	6,605,527	8/2003	Dennison et al.
AS5	6,613,604	9/2003	Maimon et al.
AT5	6,621,095	9/2003	Chiang et al.
AU5	6,625,054	9/2003	Lowery et al.
AV5	6,642,102	11/2003	Xu
AW5	6,646,297	11/2003	Dennison
AX5	6,649,928	11/2003	Dennison
AY5	6,667,900	12/2003	Lowery et al.
AZ5	6,671,710	12/2003	Ovshinsky et al.
AA6	6,673,648	1/2004	Lowrey
AB6	6,673,700	1/2004	Dennison et al.
AC6	6,674,115	1/2004	Hudgens et al.
AD6	6,687,153	2/2004	Lowery
AE6	6,687,427	2/2004	Ramalingam et al.
AF6	6,690,026	2/2004	Peterson
AG6	6,696,355	2/2004	Dennison
AH6	6,707,712	3/2004	Lowery
AI6	6,714,954	3/2004	Ovshinsky et al.

## FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	†
		Country Code <sup>2</sup> -Number <sup>3</sup> -Kind Code <sup>4</sup> (if known)				
	BA	56126916	10/19981	Akira et al.		
	BB	WO 97/48032	12/18/1997	Kozicki et al.		
	BC	WO 99/28914	06/10/1999	Kozicki et al.		
	BD	WO 00/48196	08/17/2000	Kozicki et al.		
	BE	WO 02/21542	03/14/2002	Kozicki et al.		

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**INFORMATION DISCLOSURE  
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Sheet	5	of	5	Attorney Docket Number	M4065.0704/P704
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**Complete if Known**

Application Number	09/943,199
Filing Date	August 29, 2001
First Named Inventor	Kristy A. Campbell
Group Art Unit	2818
Examiner Name	D. Vu

**OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS**

Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	CA	Kawamoto, Y., Nishida, M., Ionic Condition in As <sub>2</sub> S <sub>3</sub> -Ag <sub>2</sub> S, GeS <sub>2</sub> -GeS-Ag <sub>2</sub> S and P <sub>2</sub> S <sub>5</sub> -Ag <sub>2</sub> S Glasses, J. Non-Cryst Solids 20(1976) 393-404.	
	CB	Kozicki et al., Silver incorporation in thin films of selenium rich Ge-Se glasses, International Congress on Glass, Volume 2, Extended Abstracts, July 2001, pgs. 8-9.	
	CC	Michael N. Kozicki, 1. Programmable Metallization Cell Technology Description, February 18, 2000	
	CD	Michael N. Kozicki, Axon Technologies Corp. and Arizona State University, Presentation to Micron Technology, Inc., April 6, 2000	
	CE	Kozicki et al., Applications of Programmable Resistance Changes In Metal-Doped Chalcogenides, Electrochemical Society Proceedings, Volume 99-13, 1999, pgs. 298-309.	
	CF	Kozicki et al., Nanoscale effects in devices based on chalcogenide solid solutions, Superlattices and Microstructures, Vol. 27, No. 516, 2000, pgs. 485-488.	
	CG	Kozicki et al., Nanoscale phase separation in Ag-Ge-Se glasses, Microelectronic Engineering 63 (2002) pgs 155-159.	
	CH	Mitkova, M.; Wang, Y.; Boolchand, P., Dual chemical role of Ag as an additive in chalcogenide glasses, Phys. Rev. Lett. 83 (1999) 3848-3851.	
	CI	Miyatani, S.-y., Electrical properties of Ag <sub>2</sub> Se, J. Phys. Soc. Japan 13 (1958) 317.	

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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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		Number-Kind Code <sup>2</sup> (if known)			
	AE	6,388,324	05/14/2002	Kozicki et al.	
	AF	US 2002/0000666	01/03/2002	Kozicki et al.	
	AG	5,500,532	03/19/1996	Kozicki et al.	
	AH	6,614,049	07/09/2002	Kozicki et al.	
	AI	5,751,012	05/12/1998	Welstenholme et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				
	BA	WO 97/488032	12/18/1997	Kozicki et al.		
	BB	WO 99/28914	06/10/1999	Kozicki et al.		

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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
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	CA	Abdel-Ail, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge <sub>5</sub> As <sub>38</sub> Te <sub>57</sub> chalcogenide glass, Vacuum 59 (2000) 845-853.	
	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.	
	CC	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous alloys, Rev. Mod. Phys. 50 (1978) 209-220.	
	CD	Affif, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se <sub>75</sub> Ge <sub>25</sub> -xSbx, Appl. Phys. A 55 (1992) 167-169.	
	CE	Affif, M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor GexSe <sub>1-x</sub> , Egypt, J. Phys. 17 (1986) 335-342.	
	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag <sub>2</sub> Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.	
	CG	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.	
	CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.	
	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089.	
	CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104.	
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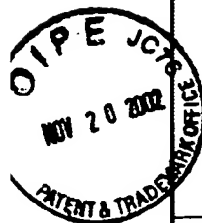
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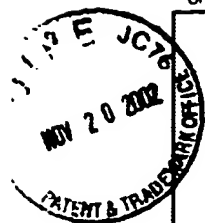
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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Application Number	
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Examiner Signature	Date Considered
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